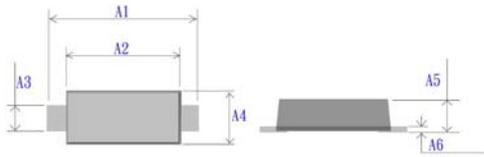


200mW SURFACE MOUNT SWITCHING DIODES



DIM	MILLIMETERS		INCHES	
	MAX	MIN	MAX	MIN
A1	1.700	1.500	0.067	0.059
A2	1.300	1.100	0.051	0.043
A3	0.350	0.250	0.014	0.010
A4	0.900	0.700	0.035	0.028
A5	0.700	0.500	0.028	0.020
A6	0.200	0.070	0.0079	0.0028

CASE : SOD-523

DIMENSIONS MILLIMETERS AND (IN INCHES)

FEATURES

- HIGH SPEED SWITCHING
- SMALL SURFACE MOUNTING TYPE.
- HIGH SPEED. ($T_{rr}=1.2ns$ Typ.)
- HIGH RELIABILITY WITH HIGH SURGE CURRENT HANDLING CAPABILITY.
- WE DECLARE THAT THE MATERIAL OF PRODUCT COMPLIANCE WITH ROHS REQUIREMENTS.

MECHANICAL DATA

- CASE : SOD-523
- SILICON EPITAXIAL PLANAR
- Pb Free: 1SS400
Halogen Free: 1SS400-H

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

RATINGS AT 25°C AMBIENT TEMPERATURE UNLESS OTHERWISE SPECIFIED.

PARAMETER	SYMBOL	1SS400	UNITS
MAXIMUM REVERSE VOLTAGE	V_R	80	V
PEAK REVERSE VOLTAGE	V_{RM}	90	V
RECTIFIED CURRENT(AVERAGE),HALF WAVE RECTIFICATION WITH RESISTIVE LOAD AND $f \geq 50Hz$	I_O	100	mA
FORWARD CURRENT(SINGLE)	I_{FM}	225	mA
JUNCTION TEMPERATURE	T_J	125	°C
OPERATING TEMPERATURE RANGE	T_{STG}	- 55 TO + 125	°C

ELECTRICAL CHARACTERISTICS (AT $T_A = 25^\circ C$ UNLESS OTHERWISE NOTED)

PARAMETER	SYMBOL	1SS400	UNITS
FORWARD VOLTAGE	$I_F=100mA$ V_F	1.2(MAX)	V
REVERSE CURRENT	$V_R= 80V$ I_R	0.1(MAX)	μA
CAPACITANCE BETWEEN TERMINALS($V_R=0.5V, f=1MHz$)	C_T	3(MAX)	pF
REVERSE RECOVERY TIME($I_F=10mA, V_R=6V; R_L=100\Omega$)	T_{RR}	4(MAX)	ns

• Electrical characteristic curves (Ta=25°C)

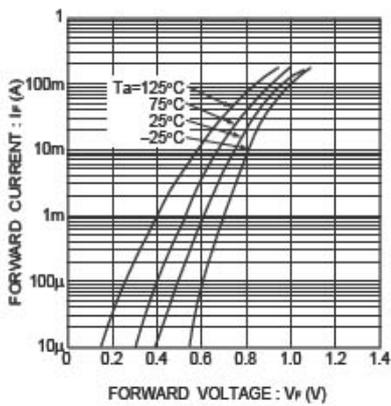


Fig.1 Forward characteristics

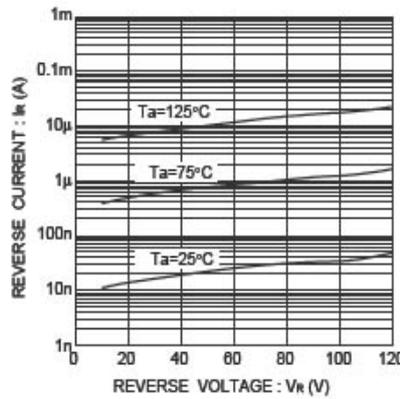


Fig.2 Reverse characteristics

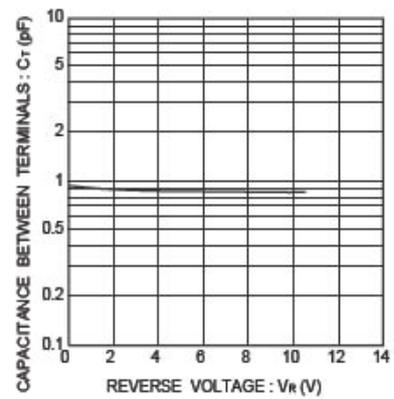


Fig.3 Capacitance between terminals characteristics

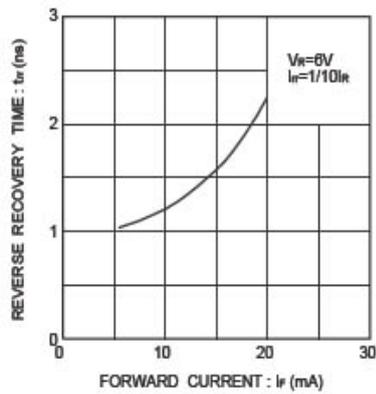


Fig.4 Reverse recovery time characteristics

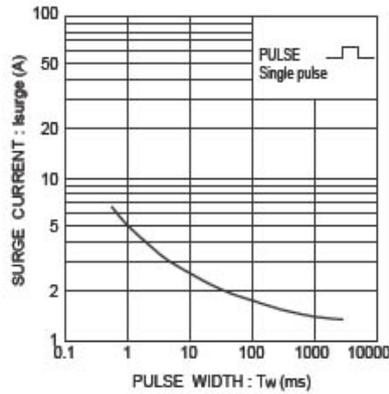


Fig.5 Surge current characteristics